

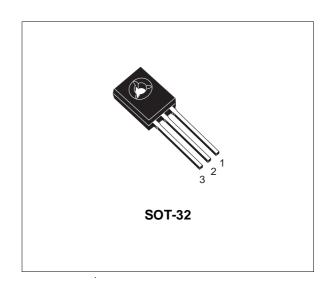
COMPLEMENTARY SILICON POWER TRANSISTORS

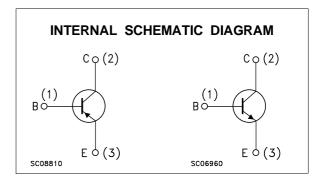
- STMicroelectronics PREFERRED SALESTYPES
- COMPLEMENTARY PNP NPN DEVICES

DESCRIPTION

The MJE172 (PNP type) and MJE182 (NPN type) are silicon Epitaxial Planar, complementary transistors in Jedec SOT-32 plastic package.

They are designed for low power audio amplifier and low current, high speed switching applications.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Value	Unit	
		NPN	MJE182		
		PNP	MJE172		
V _{CEO}	Collector-Emitter Voltage (I _B = 0)		80	V	
V _{CBO}	Collector-Base Voltage (I _E = 0)		100	V	
V _{EBO}	Base-Emitter Voltage (I _C = 0)		7	V	
Ic	Collector Current		3	Α	
I _{CM}	Collector Peak Current (t _p < 5 ms)		6	Α	
I _B	Base Current		1	Α	
P _{tot}	Total Power Dissipation at T _{case} ≤ 25 °C		12.5	W	
T _{stg}	Storage Temperature		-65 to 150	°C	
Tj	Total Power Dissipation at T _{case} ≤ 25 °C		150	°C	

For PNP type voltage and current values are negative.

September 2003

THERMAL DATA

R	R _{thj-amb}	Thermal Resistance Junction-ambient	Max	83.4	°C/W
R	thj-case	Thermal Resistance Junction-case	Max	10	°C/W

ELECTRICAL CHARACTERISTICS ($T_{case} = 25$ $^{\circ}C$ unless otherwise specified)

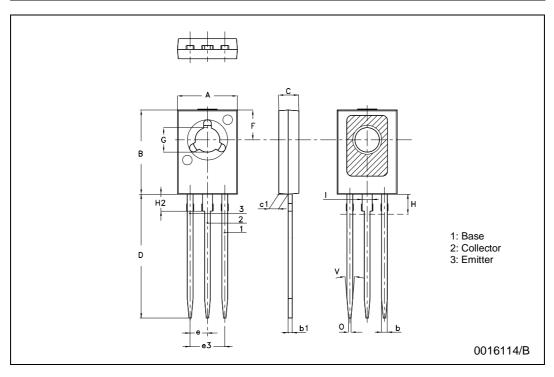
Symbol	Parameter	Test	Conditions	Min.	Тур.	Max.	Unit
I _{CBO}	Collector Cut-off Current (I _E = 0)	V_{CB} = rated V_{CB} T_{case} = 150°C	во			0.1 0.1	μA mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 7 V				0.1	μΑ
V _{CEO(sus)} *	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 10 mA		80			<
V _{CE(sat)*}	Collector-Emitter Saturation Voltage	I _C = 0.5 A I _C = 1.5 A I _C = 3 A	I _B = 50 mA I _B = 0.15 A I _B = 0.6 A			0.3 0.9 1.7	V V V
V _{BE(sat)} *	Base-Emitter on Voltage	I _C = 1.5 A I _C = 3 A	I _B = 0.15 A I _B = 0.6 A			1.5 2	V
V _{BE} *	Base-Emitter on Voltage	I _C = 0.5 A	V _{CE} = 1 V			1.2	V
h _{FE}	DC Current Gain	I _C = 0.1 A I _C = 0.5 A I _C = 1.5 A	V _{CE} = 1 V V _{CE} = 1 V V _{CE} = 1 V	50 30 12		250	
f⊤	Transistor Frequency	I _C = 0.1 A f = 10 MHz	V _{CE} = 10 V	50			MHz
С _{СВО}	Collector-base Capacitance	V _{CB} = 10 V I _E for MJE172 for MJE182	E = 0 $f = 0.1MHz$			60 40	pF pF

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^{*} Pulsed: Pulse duration = $300\mu s$, duty cycle $\leq 1.5\%$ For PNP type voltage and current values are negative.

SOT-32 (TO-126) MECHANICAL DATA

DIM.		mm			inch	
DIWI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α	7.4		7.8	0.291		0.307
В	10.5		10.8	0.413		0.425
b	0.7		0.9	0.028		0.035
b1	0.40		0.65	0.015		0.025
С	2.4		2.7	0.094		0.106
c1	1.0		1.3	0.039		0.051
D	15.4		16.0	0.606		0.630
е		2.2			0.087	
e3		4.4			0.173	
F		3.8			0.150	
G	3		3.2	0.118		0.126
Н			2.54			0.100
H2		2.15			0.084	
I		1.27			0.05	
0		0.3			0.011	_
V		10°			10°	



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